

ABSTRACT OF THE DISCLOSURE

A semiconductor method for a liquid crystal display that includes providing a substrate, providing a layer of insulating material over the substrate, depositing a layer of amorphous silicon over the layer of insulating material, crystallizing the layer of amorphous silicon to form a layer of polysilicon, treating the layer of polysilicon to change the properties of a surface of the layer of polysilicon, and smoothing the surface of the layer of polysilicon.